

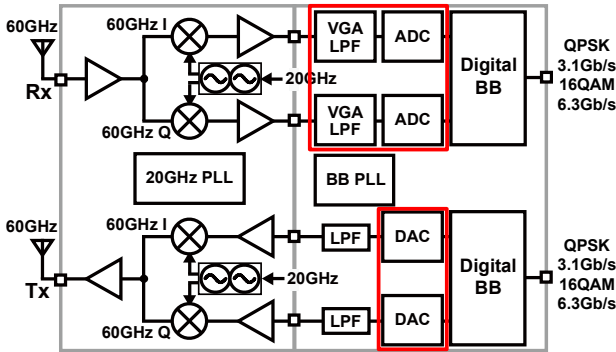
An 84 mW 0.36 mm² Analog Baseband Circuits for 60 GHz Wireless Transceiver in 40 nm CMOS

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1. Introduction

Developing an analog baseband circuitry for 60 GHz wireless transceiver in 40 nm digital CMOS.

Target Specifications



Transceiver		ADC	
Modulation	QPSK, 16QAM	Resolution	5 bit
Data rate	3.1 Gb/s (QPSK)	Sampling rate	2304 MS/s
	6.3 Gb/s (16QAM)	DNL, INL	< 0.5 LSB
Distance	> 1 m (QPSK)	SNDR	> 25 dB

VGA		DAC	
Gain range	0 - 40 dB	Resolution	6 bit
-3dB Bandwidth	~1000 MHz	Sampling rate	3456 MS/s
Input referred noise	< 4 nV/ $\sqrt{\text{Hz}}$	DNL, INL	< 0.5 LSB
SFDR@100MHz	< 40 dBc	SFDR	> 39 dBc

Design Items

VGA : Variable Gain Amplifier

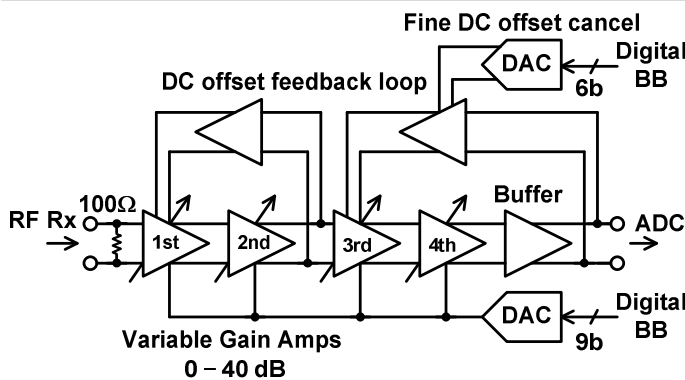
ADC : Analog to Digital Converter

DAC : Digital to Analog Converter

➤ LPF function is implemented in VGA.

➤ S/P(1/8) and P/S(1/16) circuits are implemented in ADC and DAC respectively.

2. Variable Gain Amplifier



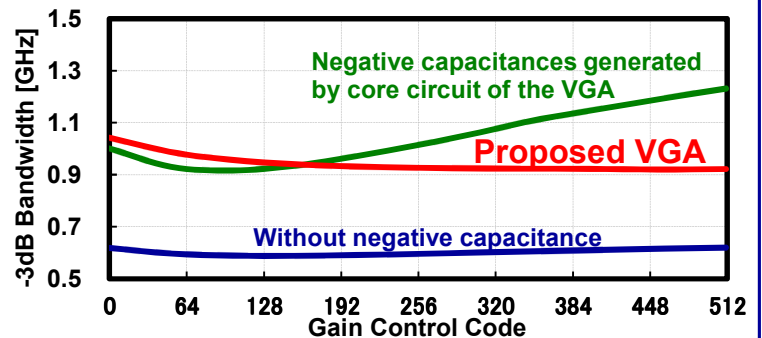
➤ 0 - 40dB gain range.

-Source degeneration resistors are controlled by 9bit DAC.

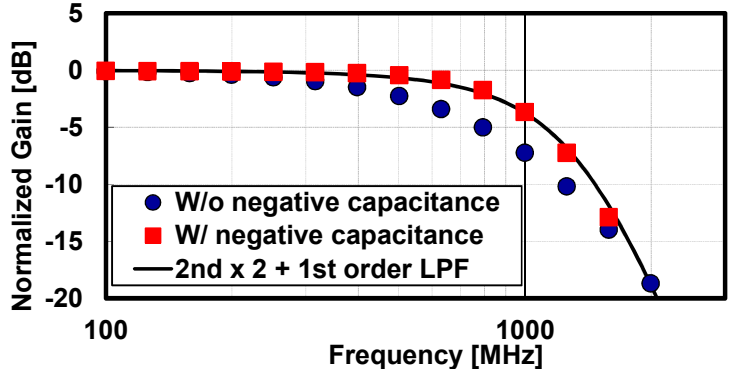
➤ 1GHz Bandwidth with LPF function.

➤ Negative capacitance used for increasing BW.

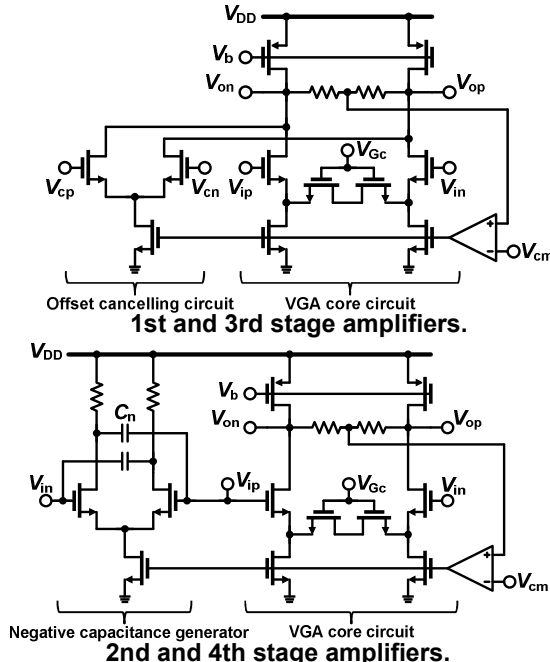
-Fixed negative capacitance used for BW flatness.



-3 dB Bandwidth vs. gain control code of the VGA

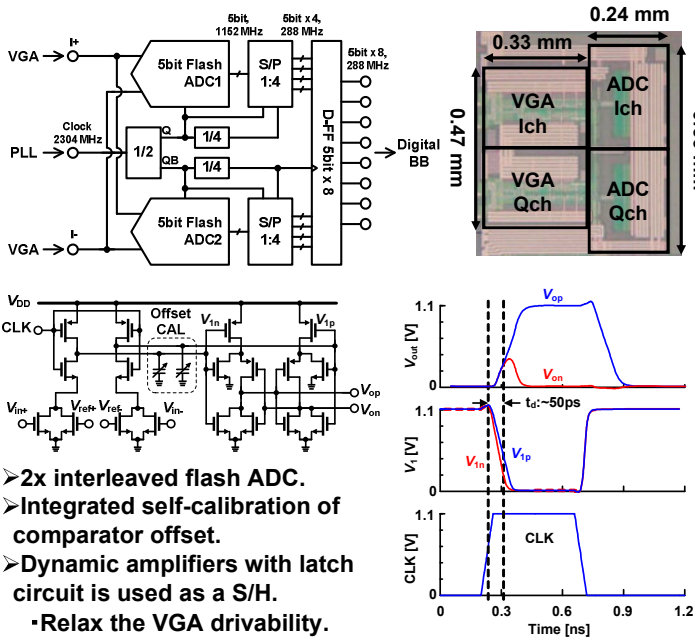


Frequency characteristic of the VGA at 20dB Gain



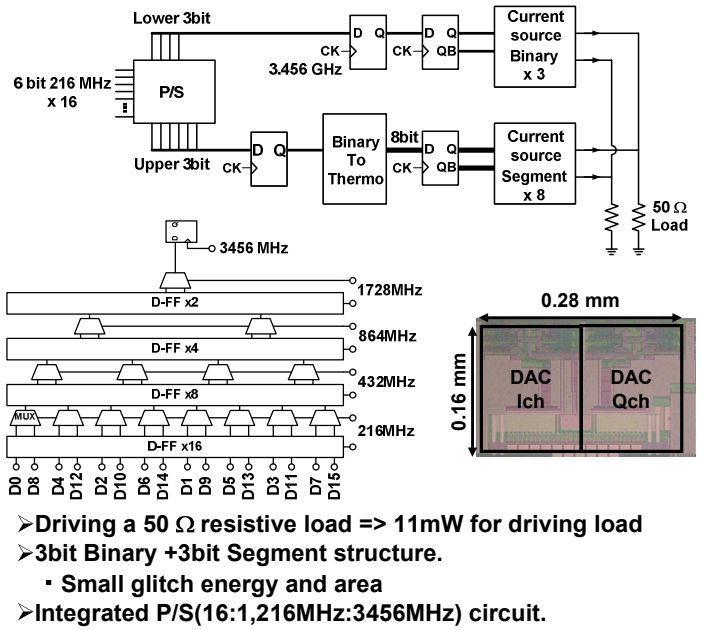
3. Analog to Digital Converter

5bit, 2304MS/s, 12mW Flash ADC



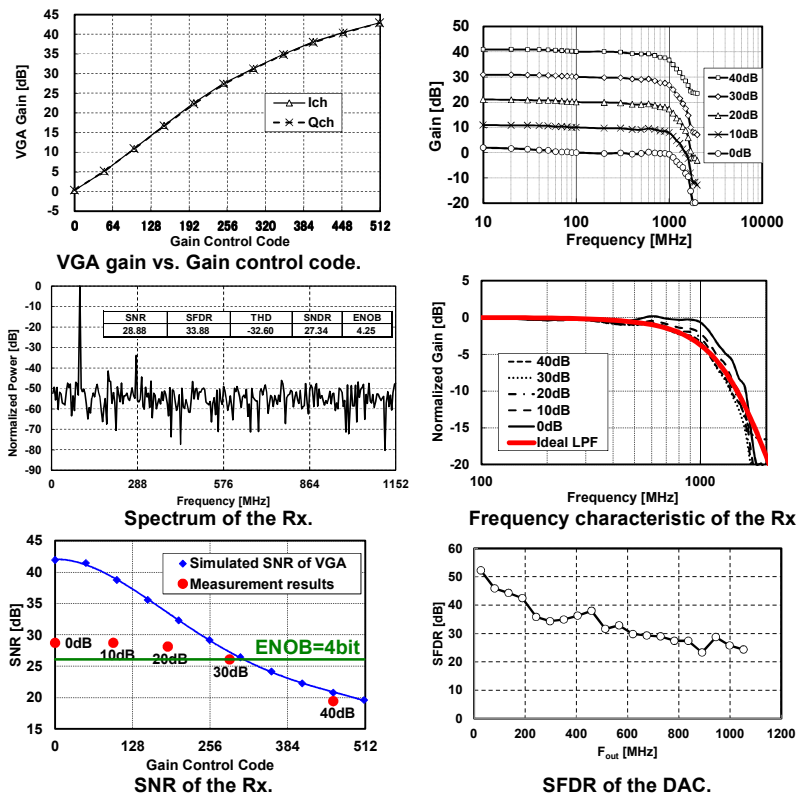
4. Digital to Analog Converter

6bit, 3456MS/s, 21mW Current steering DAC

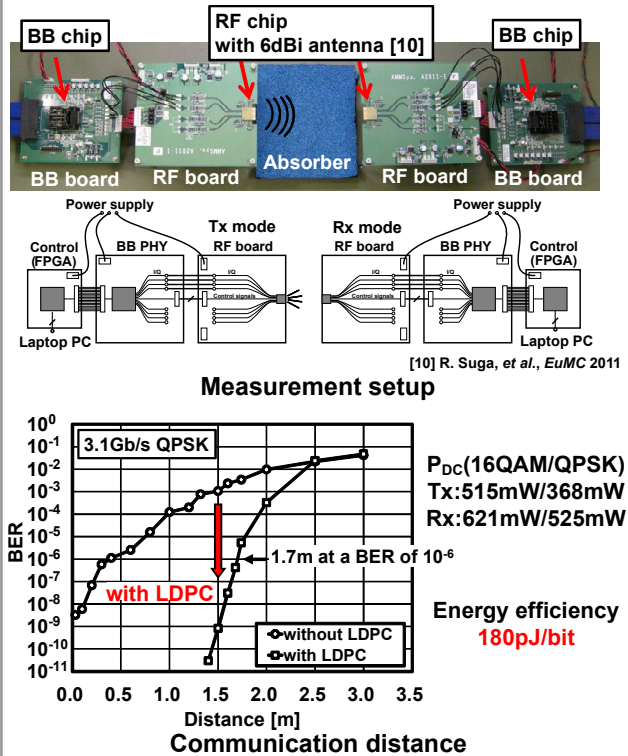


5. Measurement Results

Analog baseband Measurement results



Transceiver Measurement results



VGA performance summary

Work	Tech.	LFP Order	f-3dB	Gain	Linearity	Noise	Supply	Power
This work	40nm	2thx2+1th	920MHz@40dB 1150MHz@0dB	0dB ~40dB	IIP3=8.3dBm @0dB gain	IRN= 3.8nV/√Hz	1.1V	9mW
[1]S. D'Amico et al. -RFIC 2011	90nm	6th	915MHz@0dB	0.1dB ~19.6dB	IIP3=5.6dBm @0dB gain	IRN= -145 dBm/Hz	1V	9.5mW@0dB 10.8mW@20dB
[2]C. Wu et al. -ISSCC 2004	0.18μm	N/A	2GHz	~16dB ~34dB	N/A	N/A	1.8V	40mW
[3]H. Lee et al. -IEEE TMTT	0.18μm	N/A	900MHz	~39dB ~55dB	1dBcp=	NF=	1.8V	20.52mW

ADC performance summary

Work	Type	Integrated mW SoC	Cal.	Fs [GS/s]	SNDR [dB]	Power [mW]	FoM [fJ/c.s.]	Process [nm]	Area [mm ²]
This work	Flash	Yes	Int.	2.3	27.3	12	274	40	0.06
[4]K.Deguchi, et al., VLSI 2007	Flash	No	-	3.5	31.2	98	946	90	0.149
[5]E. Alpmann, et al., ISSCC 2009	SAR	No	Int.	2.5	34.0	50	489	45	1
[6]Y. Nakajima, et al., VLSI 2007	Folding	No	Int.	2.7	33.6	50	474	90	0.36
[7]B. Verbruggen, et al., ISSCC 2010	Pipeline	No	Ext.	2.2	31.1	2.6	40	40	0.03
[8]T. Ito, et al., A-SSCC 2010	Flash	No	Int.	3.0	27.6	36	600	65	0.25
[9]T. Mitomo, et al., ISSCC 2012	Flash	Yes	Int.	2.88	27.6	68.5	1200	65	-

RF+BB Constellation

	ch1	ch2	ch3	ch4
QPSK: 3.1Gb/s within 2.16GHz-BW				
Constellation				
SNR	14.8dB	14.8dB	15.9dB	15.8dB
BER	<10 ⁻¹¹	<10 ⁻¹¹	<10 ⁻¹¹	<10 ⁻¹¹
16QAM: 6.3Gb/s within 2.16GHz-BW				
Constellation				
SNR	14.1dB	15.3dB	15.6dB	15.1dB
BER	5.0 × 10 ⁻³	8.4 × 10 ⁻⁴	6.7 × 10 ⁻⁴	8.3 × 10 ⁻⁴